

	L #	Hits	Search Text	DBs
1	L1	166056	"438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	568	1 and (trench\$2 or trench-gate?) near (transistor or MOSFET?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	16	2 and (gate-drain or (gate near drain)) near capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	1	3 and third near (opening or trench?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L6	2	5 and (trench\$2 or trench-gate?) near (transistor or MOSFET?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L5	10	pattanayak-deva-n.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	280	((trench\$2 or trench-gate?) near (transistor or MOSFET?)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	1	7 and third near (opening or trench?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L1 0	0	7 and (reduc\$3 near (gate-drain or (gate near drain)) near capacitance).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L1 1	1627	((trench\$2 or trench-gate?) near (transistor or MOSFET?))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L1 2	35	11 and (gate-drain or (gate near drain)) near capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L1 3	6	12 and (opening or trench?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L1 4	4	12 and third near mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB